

0057-2533-2



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

HIDEKI TAKAHASHI

: GROUP ART UNIT: 2811

SERIAL NO: 09/421,217

:

FILED: OCTOBER 20, 1999

: EXAMINER: LOKE, S

FOR: INSULATED GATE SEMICONDUCTOR  
DEVICE AND MANUFACTURING  
METHOD THEREOF

9/B  
FJONES  
7-26-01

RECEIVED  
TECHNOLOGY CENTER 2800  
JUL 26 2001

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action of April 24, 2001, please amend the above-identified application as follows:

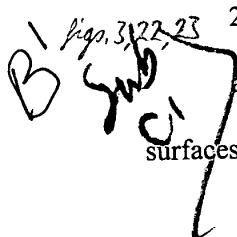
IN THE TITLE

Please amend the title to read as follows:

INSULATED GATE SEMICONDUCTOR DEVICE WITH LOW ON  
VOLTAGE AND MANUFACTURING METHOD THEREOF

IN THE CLAIMS

Please amend Claim 22 as follows. A marked-up copy follows this amendment.



22. (Amended) An insulated gate semiconductor device, comprising:

a first semiconductor layer of a first conductivity type having first and second main surfaces on opposite sides thereof;